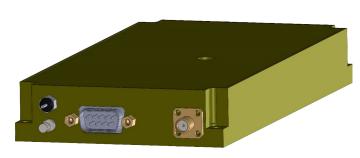


# High Efficiency Amplifier Capabilities



## Amplifiers up to 320W and 80 dB gain

### **Product Description**

UEC RF-Microwave high-efficiency RF amplifiers for 2G, 3G, 4G and 5G installations are designed to maximize power output while minimizing energy loss, which is crucial for maintaining battery life in mobile devices and reducing operational costs in base stations. We customize our high-efficiency amplifiers to meet customer specific requirements.

#### **Typical Application**

- ▶ 2G, 3G, 4G, 5G
- ▶ GSM, CDMA, LTE
- ▶ Base Stations
- Repeaters
- ► Private Networks

#### ► Gs

► High Linearity

**Features** 

- ► GaN and LDMOS Technology
- Class D and Doherty designs
- Psat up to 320 Watts
- ► Thermal Management

## Electrical Specifications ( $T_{\Delta} = 25^{\circ} C$ )

Description	UOM	Min	Typical	Max	Notes
Frequency	GHz	.002		6.00	customer to define frequency band
Small Signal Gain	dB			+80	customer defined
Gain Flatness	±dB		TBD		bandwidth dependent
Gain Variation over Temp	±dB			3	
Saturate Power (Psat)	W			320	customer defined
Max Input Power	dBm			10	
Input Dynamic Range	dB	-40		9	customer defined
Harmonics	dBc			-20	
Rise/Fall Time	nS		10		
Spurious Out	dBc			-60	
Input VSWR	:1			1.5	
Output VSWR	:1			1.5	
Voltage Range	VDC	12		48	
Current	mA			TBD	dependent on Psat and VDC